

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



# Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



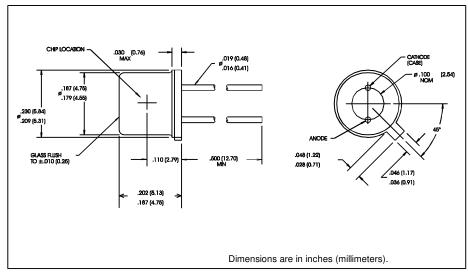






# **PIN Silicon Photodiode** Type OP910W





#### **Features**

- Wide receiving angle
- Fast switching time
- Linear response vs. irradiance
- Enhanced temperature range

### **Description**

The OP910W consists of a PIN silicon photodiode mounted in a two-leaded hermetic TO-46 package. The flat lens has an acceptance half angle of  $\pm 40^{\circ}$ .

# **Absolute Maximum Ratings** (T<sub>A</sub> = 25°C unless otherwise noted)

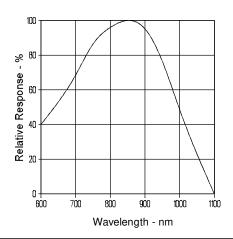
Reverse Voltage	60 V
Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-65° C to +125° C
Lead Soldering Temperature [1/16 inch (1.6mm) from case for 5 sec	c. with soldering
iron]	200°C <sup>(1)</sup>
Power Dissipation	

#### Notes:

- (1) RMA Flux is recommended. Duration can be extended to 10 sec. max. when flow
- (2) Light source is an unfiltered GaAs LED with a peak wavelength of 935 nm and a radiometric intensity level which varies less than 10% over the entire lens surface of the photodiode being tested.
- Junction temperature maintained at 25° C.
- (4) To calculate typical dark current in nA, use the formula I<sub>D</sub>=10<sup>(0.42 T</sup>A<sup>-1.5)</sup> where T<sub>A</sub> is ambient temperature in <sup>o</sup> C.
  (5) Derate linearly 2.5 mW/<sup>o</sup> C above 25<sup>o</sup> C.

#### **Typical Performance Curves**

### **Typical Spectral Response**



# Type OP910W

## **Electrical Characteristics** (T<sub>A</sub> = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITION
ΙL	Light Current	1.7	2.4		μΑ	$V_R = 20 \text{ V}, E_e = .50 \text{ mW/cm}^2 \text{ note 2, 3}$
ID	Dark Current		1	10	nA	$V_R = 20 V, E_e = 0.0$
$V_{(BR)R}$	Reverse Voltage Breakdown	100			V	$I_R = 100 \mu A$
tr	Rise Time		10		nS	V <sub>R</sub> = 20 V, R <sub>L</sub> = 50 OHMS
tf	Fall Time		10		nS	$V_R = 20 \text{ V}, R_L = 50 \text{ OHMS}$
Ø	Half Angle		+/-40		degr.	I <sub>F</sub> = Constant
СР	Capacitance		13		pF	$V_R = 0 V, F = 1 Mhz, E_e = 0$
V <sub>F</sub>	Forward Voltage			1.2	V	I <sub>F</sub> = 100 mA

### **Typical Performance Curves**

